

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF1002MB** is Designed for Class C, DME/TACAN Applications up to 1150 MHz.

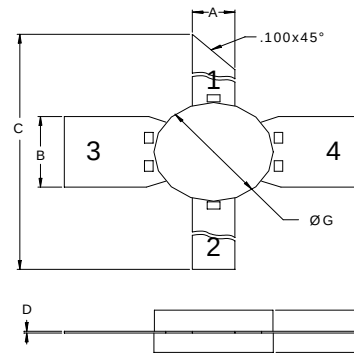
FEATURES:

- Class C Operation
- $P_G = 9.0$ dB at 2.0 W/1150 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	250 mA
V_{CEO}	20 V
V_{CBO}	50 V
P_{DISS}	7.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	25°C/W

PACKAGE STYLE .280 4L PILL (A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	.195 / 4.95	.205 / 5.21
C	1.000 / 25.40	
D	.004 / 0.10	.007 / 0.18
E	.050 / 1.27	.065 / 1.65
F		.145 / 3.68
G	.275 / 6.99	.285 / 7.21

1 = COLLECTOR 2 = EMITTER 3 & 4 = BASE

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 5.0$ mA	20			V
BV_{CBO}	$I_C = 5.0$ mA	50			V
BV_{CES}	$I_C = 5.0$ mA	50			V
BV_{EBO}	$I_E = 1.0$ mA	3.5			V
I_{CBO}	$V_{CB} = 35$ V			0.5	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ A	10		100	---
C_{OB}	$V_{CB} = 35$ V $f = 1.0$ MHz		2.5	5.0	pF
P_G	$V_{CC} = 35$ V $P_{OUT} = 2.0$ W $f = 1090$ MHz	10	12		dB
η_C		40	35		%